HSQ Series RF High Q Multilayer Chip Ceramic Capacitor

1. Capacitor characteristics and applications

1.1 Characteristics

- Size specifications are standardized and suitable for surface mount components in hybrid integrated circuits or printed circuits
- High Q value, low ESR, high reliability
- Low loss, high capacitance stability, high operating frequency
- Suitable for high-frequency circuits, VHF-microwave bands, RF and amplification circuits in various equipment

1.2 Main performance indicators

- Temperature coefficient: C0G: 0±30ppm/℃
- Capacitance drift: no more than±0.2% or ±0.05pF,whichever is larger.
- Quality factor (Q value): greater than 2,000 at a frequency of 1mHz/1kHz
- Insulation resistance:>100000mQ at 20℃
- Operating temperature:-55~125℃

2. Product model naming

How to order

HHQ	1111	C0G	1R0	B	501	N	T
Product series	Size specifications	Type of Dielectric	Capacitance (unit: pF)	Tolerance	Rated voltage	Termination	Packaging form
HSQ series RF high Q capacitor	0402 1111 0603 2525 3838 0805 0505 0709	C0G: +30ppm/℃	The first two digits are significant figures, and the last digit is the power of 10	A :±0.05pF B :+0.10pF C :+0.25pF D :±0.50pF F :+1.0% G :±2.0% J :+5.0% K :±10.0%	The first two digits are significant figures, and the last digit is the power of 10	N:Leading-out Terminal: Ag/Ni/Sn Z: Leading-out Terminal: Ag/Ni/SnPb E: Non-magnetic Terminal M: MMicrostrip A: Axial tape RW: Radial wire RN: Non-magnetic radial wire	T: Tape & reel C: Cut Tray B: Bulk